



August 2014

# FDPF44N25T

## N-Channel UniFET™ MOSFET

250 V, 44 A, 69 mΩ

### Features

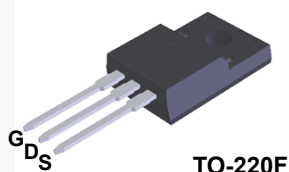
- $R_{DS(on)}$  = 69 mΩ (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 22 A
- Low Gate Charge (Typ. 47 nC)
- Low  $C_{rss}$  (Typ. 60 pF)

### Applications

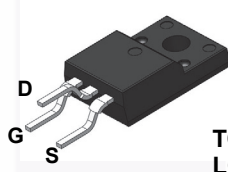
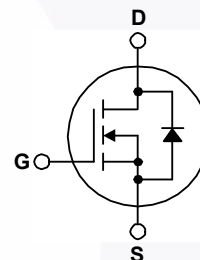
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220F

TO-220F  
LG-formed

### Absolute Maximum Ratings

 $T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol         | Parameter  |  | FDPF44N25T<br>FDPF44N25TRDTU | Unit                |
|----------------|--|--|------------------------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage   |  | 250                          | V                   |
| $I_D$          | Drain Current  | - Continuous ( $T_C = 25^\circ\text{C}$ )  | 44*                          | A                   |
|                |  | - Continuous ( $T_C = 100^\circ\text{C}$ ) | 26.4*                        | A                   |
| $I_{DM}$       | Drain Current  | - Pulsed (Note 1)                          | 176*                         | A                   |
| $V_{GSS}$      | Gate-Source voltage  |  | $\pm 30$                     | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy                                       |  | 2055                         | mJ                  |
| $I_{AR}$       | Avalanche Current  |  | 44                           | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy  |  | 30.7                         | mJ                  |
| $dv/dt$        | Peak Diode Recovery $dv/dt$  |  | 4.5                          | V/ns                |
| $P_D$          | Power Dissipation  | ( $T_C = 25^\circ\text{C}$ )               | 38                           | W                   |
|                |  | - Derate Above $25^\circ\text{C}$          | 0.3                          | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                              |  | -55 to +150                  | $^\circ\text{C}$    |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds |  | 300                          | $^\circ\text{C}$    |

\*Drain current limited by maximum junction temperature.

### Thermal Characteristics

| Symbol          | Parameter                                     | FDPF44N25T<br>FDPF44N25TRDTU | Unit               |
|-----------------|---|------------------------------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max.    | 3.3                          | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5                         |                    |

## Package Marking and Ordering Information

| Part Number    | Top Mark   | Package                | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|------------|------------------------|----------------|-----------|------------|----------|
| FDPF44N25T     | FDPF44N25T | TO-220F                | Tube           | N/A       | N/A        | 50 units |
| FDPF44N25TRDTU | FDPF44N25T | TO-220F<br>(LG-formed) | Tube           | N/A       | N/A        | 50 units |

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol   | Parameter   | Conditions  | Min.     | Typ.     | Max.    | Unit     |
|--|---|---|----------|----------|---------|----------|
| Off Characteristics                                    |   |   |          |          |         |          |
| BV <sub>DSS</sub>                                      | Drain-Source Breakdown Voltage                        | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA, T <sub>J</sub> = 25°C                             | 250      | --       | --      | V        |
| ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>                   | Breakdown Voltage Temperature Coefficient             | I <sub>D</sub> = 250 μA, Referenced to 25°C   | --       | 0.25     | --      | V/°C     |
| I <sub>DSS</sub>                                       | Zero Gate Voltage Drain Current                       | V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C | --<br>-- | --<br>-- | 1<br>10 | μA<br>μA |
| I <sub>GSSF</sub>                                      | Gate-Body Leakage Current, Forward                    | V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V   | --       | --       | 100     | nA       |
| I <sub>GSSR</sub>                                      | Gate-Body Leakage Current, Reverse                    | V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V  | --       | --       | -100    | nA       |
| On Characteristics                                     |   |   |          |          |         |          |
| V <sub>GS(th)</sub>                                    | Gate Threshold Voltage                                | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                       | 3.0      | --       | 5.0     | V        |
| R <sub>DS(on)</sub>                                    | Static Drain-Source On-Resistance                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22 A   | --       | 0.058    | 0.069   | Ω        |
| g <sub>FS</sub>  | Forward Transconductance                              | V <sub>DS</sub> = 40 V, I <sub>D</sub> = 22 A   | --       | 32       | --      | S        |
| Dynamic Characteristics                                |   |   |          |          |         |          |
| C <sub>iss</sub>                                       | Input Capacitance                                     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1.0 MHz                                     | --       | 2210     | 2870    | pF       |
| C <sub>oss</sub>                                       | Output Capacitance                                    |   | --       | 450      | 585     | pF       |
| C <sub>rss</sub>                                       | Reverse Transfer Capacitance                          |   | --       | 60       | 90      | pF       |
| Switching Characteristics                              |   |   |          |          |         |          |
| t <sub>d(on)</sub>                                     | Turn-On Delay Time                                    | V <sub>DD</sub> = 125 V, I <sub>D</sub> = 44 A,<br>R <sub>G</sub> = 25 Ω<br><br>(Note 4)          | --       | 53       | 117     | ns       |
| t <sub>r</sub>   | Turn-On Rise Time                                     |   | --       | 402      | 814     | ns       |
| t <sub>d(off)</sub>                                    | Turn-Off Delay Time                                   |   | --       | 85       | 179     | ns       |
| t <sub>f</sub>   | Turn-Off Fall Time                                    |   | --       | 112      | 234     | ns       |
| Q <sub>g</sub>   | Total Gate Charge                                     | V <sub>DS</sub> = 200 V, I <sub>D</sub> = 44 A,<br>V <sub>GS</sub> = 10 V<br><br>(Note 4)         | --       | 47       | 61      | nC       |
| Q <sub>gs</sub>  | Gate-Source Charge                                    |   | --       | 18       | --      | nC       |
| Q <sub>gd</sub>  | Gate-Drain Charge                                     |   | --       | 24       | --      | nC       |
| Drain-Source Diode Characteristics and Maximum Ratings |   |   |          |          |         |          |
| I <sub>S</sub>   | Maximum Continuous Drain-Source Diode Forward Current |   | --       | --       | 44      | A        |
| I <sub>SM</sub>  | Maximum Pulsed Drain-Source Diode Forward Current     |   | --       | --       | 176     | A        |
| V <sub>SD</sub>  | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 44 A  | --       | --       | 1.4     | V        |
| t <sub>rr</sub>  | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 44 A,<br>dI <sub>F</sub> /dt =100 A/μs                    | --       | 195      | --      | ns       |
| Q <sub>rr</sub>  | Reverse Recovery Charge                               |   | --       | 1.8      | --      | μC       |

### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 1.7\text{ mH}$ ,  $I_{AS} = 44\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 44\text{ A}$ ,  $dI/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

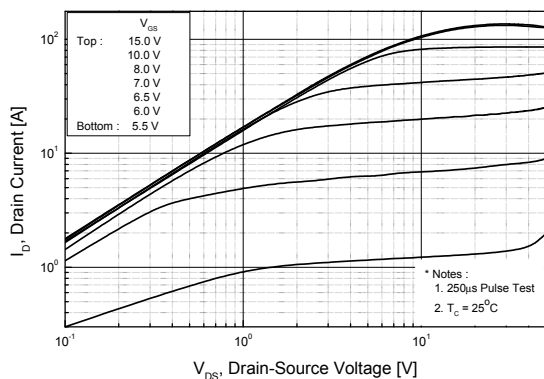


Figure 2. Transfer Characteristics

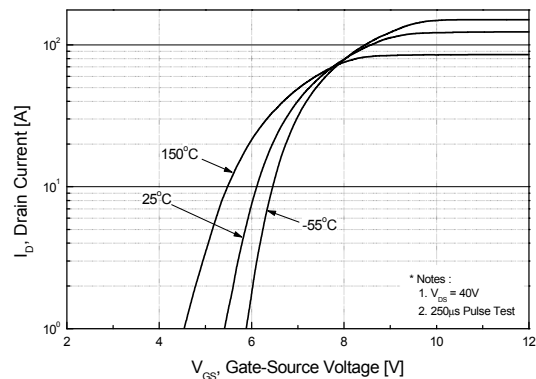


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

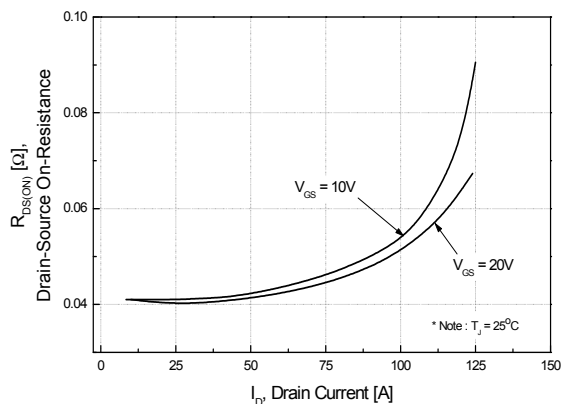


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

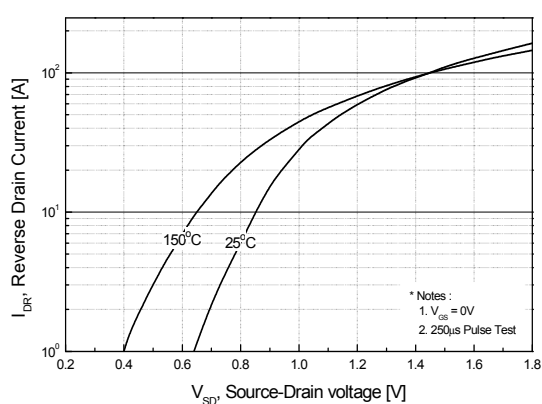


Figure 5. Capacitance Characteristics

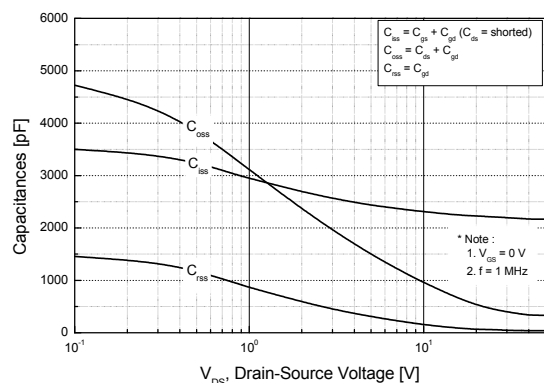
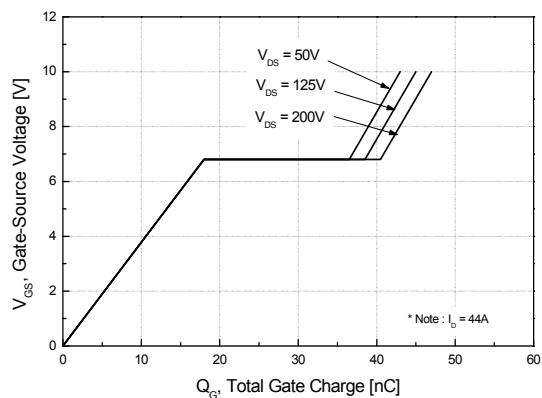
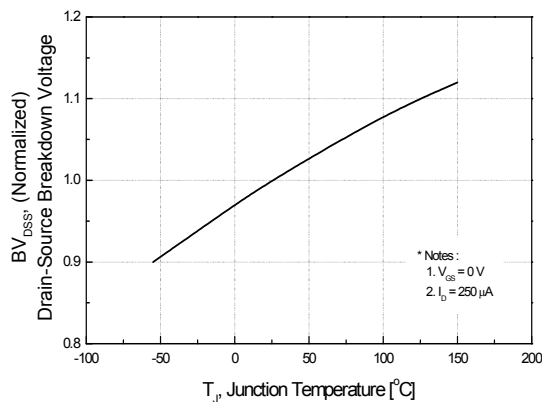


Figure 6. Gate Charge Characteristics

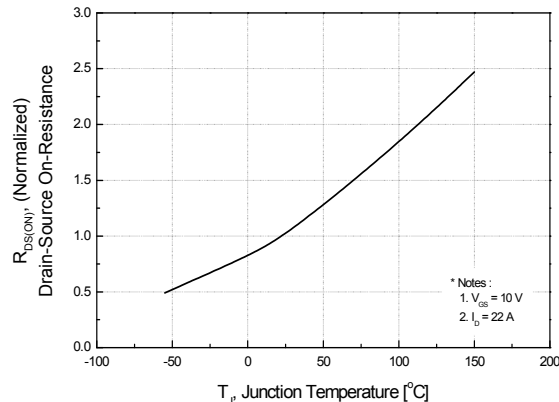


## Typical Performance Characteristics (Continued)

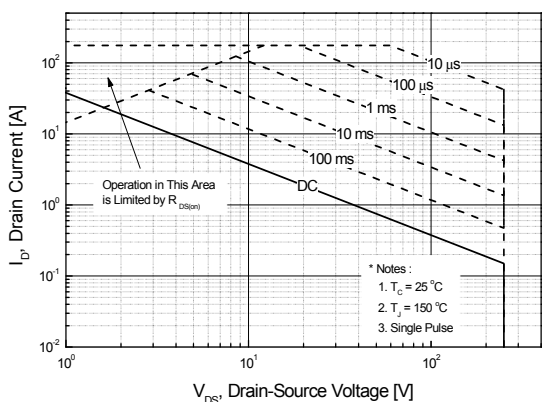
**Figure 7. Breakdown Voltage Variation vs. Temperature**



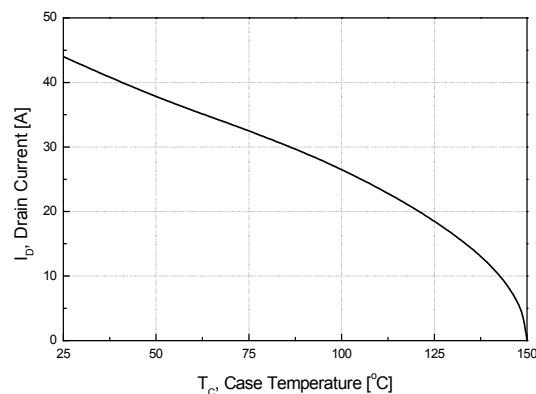
**Figure 8. On-Resistance Variation vs. Temperature**



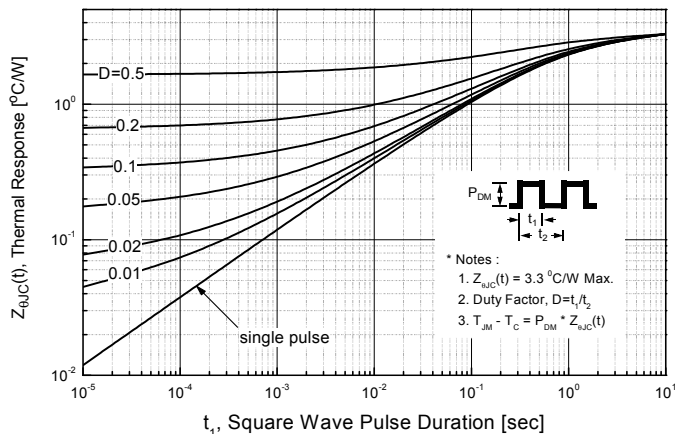
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**



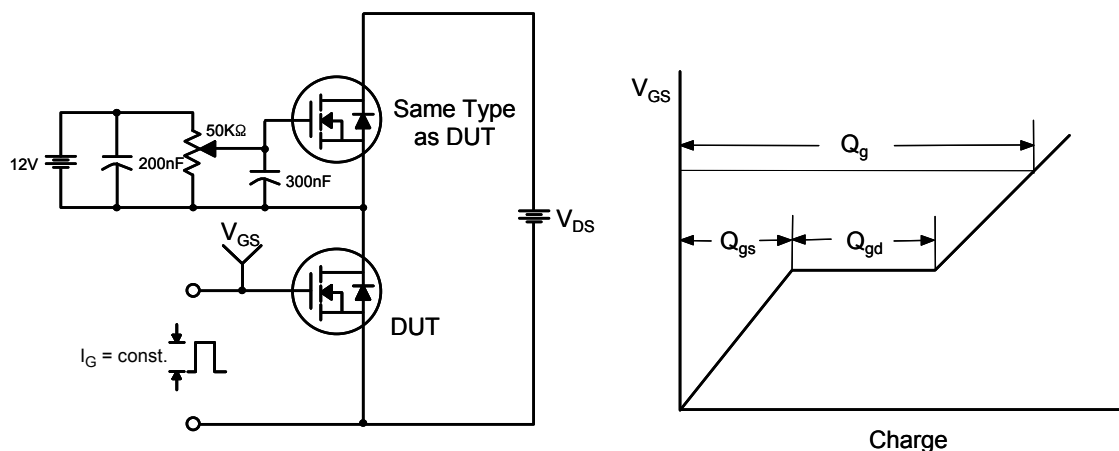


Figure 12. Gate Charge Test Circuit & Waveform

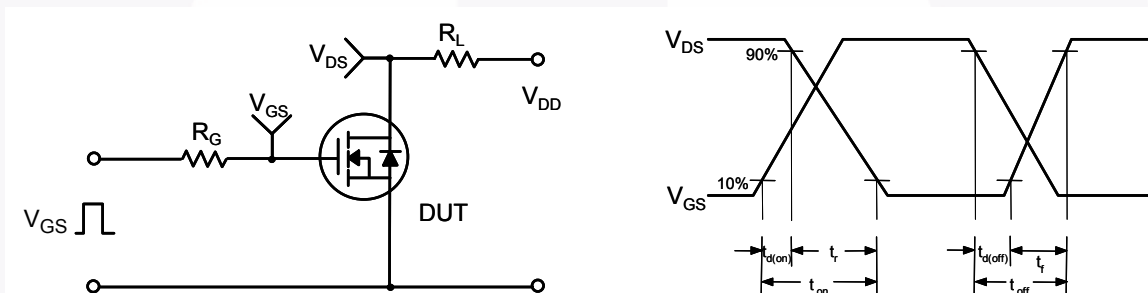


Figure 13. Resistive Switching Test Circuit & Waveforms

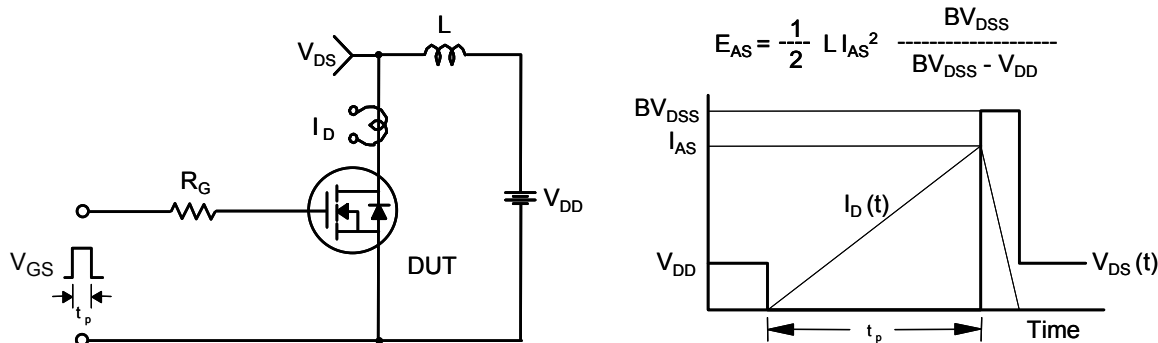


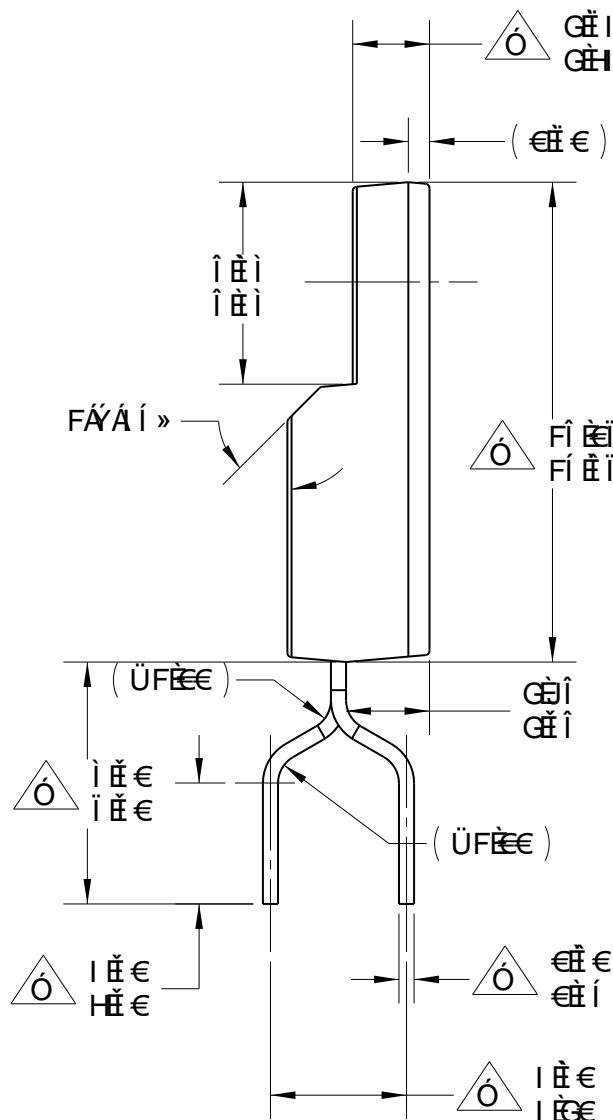
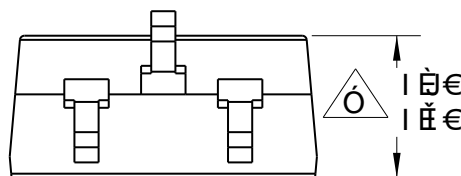
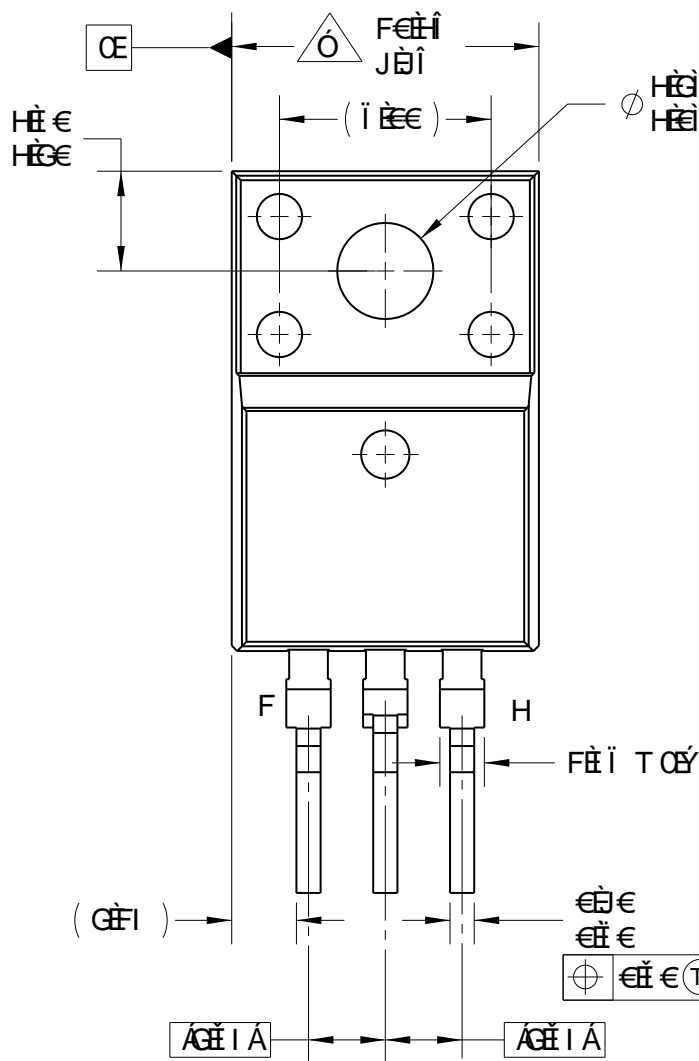
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

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